

MEMORY FORMING METHOD AND MEMORY

ABSTRACT

A method for forming a memory and a memory are provided. According to the method, a substrate (100) in which substrate (100) at least word line structures (102) and active regions (101) are included, as well as a bottom dielectric layer (110) and bit line contact layers (121) that are on a top surface of the substrate (100), is provided, the bit line contact openings (111) being provided in the bottom dielectric layer (110), the bit line contact openings (111) exposing the active regions (101) in the substrate (100), and the bit line contact layers (121) covering the bottom dielectric layer (110) and filling the bit line contact openings (111); part of the bit line contact layers (121) are etched to form bit line contact layers (121) at different heights; conducting layers (140) are formed, top surfaces of the conducting layers (140) being at different heights in a direction perpendicular to an extension direction of the word line structure (102), and the top surfaces of the conducting layers (140) being at different heights in the extension direction of the word line structure (102); top dielectric layers (150) are formed; and etching is performed to form separate bit line structures (200).

(Fig. 13)